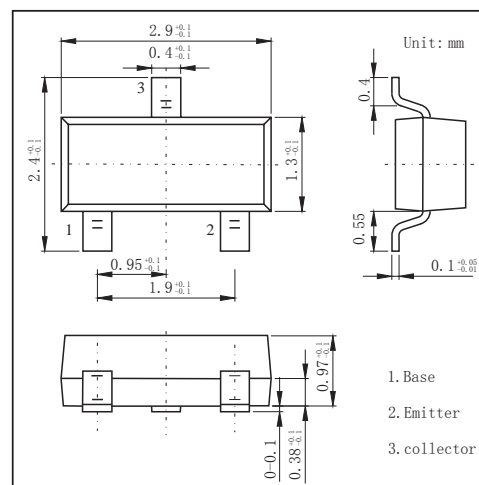


SOT-23 Plastic-Encapsulate Transistors
FEATURES

- High breakdown voltage
- PNP Transistors

MECHANICAL DATA

- Case style:SOT-23 -3molded plastic
- Mounting position:any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-55	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-150	mA
Collector dissipation	P _C	200	mW
Jumction temperature	T _j	150	°C
Storage temperature	T _{stg}	-50 to 150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _C = -100uA , I _E = 0A	-55			V
Collector-emitter breakdown voltage	V _{CEO}	I _C = - 1 mA , I _B = 0 A	-50			V
Emitter-base breakdown voltage	V _{EBO}	I _E = -100uA , I _C = 0A	-5			V
Collector cutoff current	I _{CB0}	V _{CB} = - 3.5 V , I _E = 0A			-0.1	uA
Emitter cutoff current	I _{EBO}	V _{EB} = - 4 V , I _C = 0			-0.1	uA
DC current Gain	h _{FE}	V _{CE} = - 6 V , I _C = -1mA	200		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = - 50 mA , I _B = -5mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = - 50 mA , I _B = -5mA			-1.0	V
Output capacitance	C _{ob}	V _{CB} = - 6 V , I _E =0 , f = 1MHz		4.0		pF
Transition frequency	f _T	V _{CE} = - 6 V , I _C = -10mA		180		MHz